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thin solid films

Contents

Publication schedule v

OPTICAL THIN FILMS

Transparent conducting optical coatings

Annealing and Sb-doping of Sn–O films produced by filtered vacuum arc deposition: structure and electro-optical properties 1
L. Kaplan, A. Ben-Shalom, R. L. Boxman, S. Goldsmith, U. Rosenberg and M. Nathan (Tel-Aviv, Israel)

Preparation of conductive ZnO:Al films by a facing target system with a strong magnetic field 9
K. Tominaga, M. Kataoka, T. Ueda, M. Chong, Y. Shintani and I. Mori (Tokushima, Japan)

Preparation of milky transparent conducting ZnO films with textured surface by atmospheric chemical vapour deposition using $Zn(C_5H_7O_2)_2$ 14
T. Minami, H. Sato, H. Sonohara, S. Takata, T. Miyata and I. Fukuda (Ishikawa, Japan)

Optical quantum size effects in diamond-like carbon superlattice structures 20
S. R. P. Silva, G. A. J. Amaratunga, Rusli (Cambridge, UK), S. Haq (Bristol, UK) and E. Salje (Cambridge, UK)

Fundamental aspects of optical thin films

Optical analysis of complex multilayer structures using multiple data types 25
B. D. Johs, W. A. McGahan and J. A. Woollam (Lincoln, NE, USA)

Laser-assisted deposition of optical coatings 28
P. Thomsen-Schmidt, D. Schäfer (Berlin, Germany), B. Steiger, H. Braußе (Mittewida, Germany), H. Johansen and T. Martini (Halle, Germany)

Decorative optical coatings 33
G. Reiners, U. Beck (Berlin, Germany) and H. A. Jehn (Schwäbisch-Gmünd, Germany)

Spatially resolved densification of solution deposited zirconium dioxide films by laser irradiation 41
G. J. Exarhos, L. Q. Wang (Richland, WA, USA) and T. Dennis (Houston, TX, USA)

Effects of ion beam irradiation on the properties and epitaxial growth of aluminium nitride film by the ion beam assisted deposition process 47
I.-H. Kim and S.-H. Kim (Pohang, South Korea)

Semiconductor related optical materials

$Ba_xSr_{1-x}TiO_3$ thin films by a chemical process 53
Z. A. Burhanuddin, M. S. Tomar and E. Dayalan (Tulsa, OK, USA)

Modified Forouhi and Bloomer dispersion model for the optical constants of amorphous hydrogenated carbon thin films 57
W. A. McGahan, T. Makovicka, J. Hale and J. A. Woollam (Lincoln, NE, USA)

Amorphous Si thin films prepared by vacuum arc deposition 62
D. Arbilly, R. L. Boxman, S. Goldsmith, A. Rothwarf and L. Kaplan (Tel-Aviv, Israel)

Characterization of p-$CuGa_{0.25}In_{0.75}Se_2$/n-$Zn_{0.35}Cd_{0.65}S$ polycrystalline thin film heterojunctions 67
Y. Aparna, B. Srinivasulu Naidu and P. J. Reddy (Tirupati, India)

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DIAMOND RELATED MATERIALS

Synthesis, characterization and applications of cubic boron nitride

Cross-section transmission electron microscopy observations of c-BN films deposited on Si by ion-beam-assisted deposition 72
H. Yamashita, K. Kuroda, H. Saka (Nagoya, Japan), N. Yamashita, T. Watanabe and T. Wada (Yokohama, Japan)

Synthesis and structural characterization of boron nitride thin films 78
M. Elena, L. Guzman, L. Calliari, L. Moro (Povo, Italy), A. Steiner (Ispra, Italy), A. Miotello, M. Bonelli (Trento, Italy), R. Capelletti (Parma, Italy) and P. M. Ossi (Trento, Italy)

Physical properties of nitrogenated amorphous carbon films produced by ion-beam-assisted deposition..... 85
F. Rossi (Petten, Netherlands), B. Andre (Grenoble, France), A. van Veen, P. E. Mijnarends, H. Schut, F. Labohm (Delft, Netherlands), M. P. Delplancke (Bruxelles, Belgium), H. Dunlop (Voreppe, France) and E. Anger (Villetaneuse, France)

Carbon nitride formation by low-energy nitrogen implantation into graphite 90
I. Gouzman, R. Brener and A. Hoffman (Haifa, Israel)

Synthesis and characterization of diamond and related materials

Diamond coatings from a solid carbon source..... 95
S. Jou, H. J. Doerr and R. F. Bunshah (Los Angeles, CA, USA)

Optimizing the gas phase chemistry in a d.c. arcjet diamond chemical vapor deposition reactor..... 103
S. W. Reeve and W. A. Weimer (China Lake, CA, USA)

Deposition of white diamond thin films by increasing the total pressure in a microwave-plasma-enhanced vapour deposition system..... 109
S. H. Kim, Y. S. Park and J.-W. Lee (Suwin, South Korea)

Nucleation studies of thin diamond films on model substrates 114
J. Patscheider and B. Oral (Dübendorf, Switzerland)

Internal stress of chemical vapour deposition diamond film on silicon 119
Y. H. Chiou, C. T. Hwang, M. Y. Han, J. H. Jou, Y. S. Chang and H. C. Shih (Hsinchu, Taiwan)

Elastic modulus of diamond-like carbon films prepared by pulsed vacuum arc..... 125
B. Schultrich, H.-J. Scheibe, G. Grandremy, D. Schneider and P. Siemroth (Dresden, Germany)

Effects of ambient conditions on the adhesion of cubic boron nitride films on silicon substrates 130
G. F. Cardinale (Davis, CA, USA), P. B. Mirkarimi, K. F. McCarthy, E. J. Klaus, D. L. Medlin, W. M. Clift (Livermore, CA, USA) and D. G. Howitt (Davis, CA, USA)

Electronic and optical applications of diamond and related materials

Comparative study of trimethylboron doping of hot filament chemically vapour deposited and microwave plasma chemically vapour deposited diamond films 136
M. C. Polo, J. Cifre, J. Puigdollers and J. Esteve (Barcelona, Spain)

Electrical properties of diamond thin films grown by chemical vapor deposition technique 141
A. K. Kulkarni, A. Shrotriya, P. Cheng, H. Rodrigo, R. Bashyam and D. J. Keeble (Houghton, MI, USA)

Use of space-charge-limited current to evaluate the electronic density of states in diamond-like carbon thin films 146
S. R. P. Silva and G. A. J. Amaratunga (Cambridge, UK)

Fabrication of an electron multiplier utilizing diamond films 151
G. T. Mearini, I. L. Krainsky, Y. X. Wang, J. A. Dayton, Jr. (Cleveland, OH, USA), R. Ramesham and M. F. Rose (Auburn, AL, USA)

The effects of impurities on the IR absorption of chemically vapour deposited diamond 157
K. M. McNamara (Schenectady, NY, USA), B. E. Scruggs and K. K. Gleason (Cambridge, MA, USA)

Optical characterization of diamond synthesized using CH_4–CO_2 gas mixtures without supplying hydrogen gas..... 162
C.-F. Chen, S.-H. Chen, T.-M. Hong and J.-S. Leu (Hsinchu, Taiwan)

Study of the loss of pattern definition in diamond growth 168
C.-F. Chen and S.-H. Chen (Hsinchu, Taiwan)

TRIBOLOGICAL COATINGS/SURFACE MODIFICATIONS

Mechanical processes on the atomic scale

Coatings tribology: a concept, critical aspects and future directions. 173
K. Holmberg (Espoo, Finland) and A. Matthews (Hull, UK)

Electrostatic-based model for alumina surfaces. 179
F. H. Streitz and J. W. Mintmire (Washington, DC, USA)

Molecular dynamics simulations of friction in self-assembled monolayers. 185
K. J. Tupper and D. W. Brenner (Washington, DC, USA)

Atomic-scale friction measurements on silver and chemisorbed oxygen surfaces 190
C. Mak, C. Daly and J. Krim (Boston, MA, USA)

Triboscopic description of local wear phenomena under an AFM tip. 194
J. L. Loubet, M. Belin, R. Durand and H. Pascal (Écully, France)

Plastic deformation in atomic size contacts. 199
N. Agraït, J. G. Rodrigo, G. Rubio, C. Sirvent and S. Vieira (Madrid, Spain)

ADVANCES IN COATING AND THIN FILM CHARACTERIZATION

Mechanical properties and film adhesion

Mechanical property characterization of thin films using spherical tipped indenters. 204
M. V. Swain and J. Menčík (Lindfield, NSW, Australia)

Effects of activated reactive evaporation process parameters on the microhardness of polycrystalline silicon carbide thin films 212
Y. C. Cha, G. Kim, H. J. Doerr and R. F. Bunshah (Los Angeles, CA, USA)

Enhanced mechanical hardness in compositionally modulated Fe(001)/Pt(001) and Fe(001)/Cr(001) epitaxial thin films. . 218
B. J. Daniels, W. D. Nix and B. M. Clemens (Stanford, CA, USA)

Nondestructive and in-situ characterization

Microstructure and thermal conductivity of epitaxial AlN thin films. 223
P. K. Kuo, G. W. Auner and Z. L. Wu (Detroit, MI, USA)

Holographic and spectroscopic characterization of spiropyran doped poly(methyl methacrylate) films. 228
S. S. Xue, G. Manivannan and R. A. Lessard (Cité Universitaire, Que., Canada)

Emittance characterization of thermal control paints, coatings and surfaces using a calorimetric technique 233
D. A. Jaworske (Cleveland, OH, USA)

Characterization of thin film ZnO/ZnCdS/$CuGaSe_2$ heterojunctions 238
K. T. R. Reddy, and P. J. Reddy (Tirupati, India)

Characterization of laser-ablated boron nitride thin films on silicon 243
R. W. Pryor, Z. L. Wu, K. R. Padmanabhan, S. Villanueva and R. L. Thomas (Detroit, MI, USA)

Atmosphere influence on in-situ ion beam analysis of thin film growth 247
Y. Lin, A. R. Krauss (Argonne, IL, USA), R. P. H. Chang (Evanston, IL, USA), O. H. Auciello (Triangle Park, NC, USA), D. M. Gruen (Argonne, IL, USA) and J. A. Schultz (Houston, TX, USA)

Opening and closing of channels during phase transitions in Al–Mn thin films 254
J. Reyes-Gasga and R. García (México, México)

Growth of low and high refractive index dielectric layers as studied by in situ ellipsometry. 257
V. Nguyen Van, S. Fisson, J. M. Frigerio, J. Rivory, G. Vuye, Y. Wang and F. Abelès (Paris, France)

Numerical ellipsometry: enhancement of new algorithms for real-time, in situ film growth monitoring 262
F. K. Urban III and J. C. Comfort (Miami, FL, USA)

Surface and thin film analysis

Use of valence band Auger electron spectroscopy to study thin film growth: oxide and diamond-like carbon films 269
H. J. Steffen (Dresden, Germany)

A new interpretation of the binding energies in X-ray photoelectron studies of oxides 277
T. L. Barr, S. Seal, L. M. Chen (Milwaukee, WI, USA) and C. C. Kao (Upton, NY, USA)

Effects of hydrogen annealing, sulfur segregation and diffusion on the cyclic oxidation resistance of superalloys: a review 285
J. L. Smialek, D. T. Jayne (Cleveland, OH, USA), J. C. Schaeffer and W. H. Murphy (Cincinnati, OH, USA)

Interfacial reactions in dynamically heated Si/Me/Si sandwich layers..... 293
A. Zalar (Ljubljana, Slovenia), S. Hofmann, F. Pimentel (Stuttgart, Germany) and P. Panjan (Ljubljana, Slovenia)

Characterization of TiO_2/SiO_2 multilayers by high resolution transmission electron microscopy and electron energy loss spectroscopy 299
K. Yu-Zhang (Noisy-le-Grand, France), G. Boisjolly (Saint-Maur, France), J. Rivory (Paris, France), L. Killian (Reims, France) and C. Colliex (Orsay, France)

Microstructural characterization and imaging techniques

Structural morphology examination of sol–gel deposited TiO_2 films 303
M. Anast, Å. Jamting, J. M. Bell and B. Ben-Nissan (Sydney, NSW, Australia)

Aspects of the surface roughness of ceramic bonding tools on a nanometer scale investigated with atomic force microscopy 308
J. Burger (Neuchâtel, Switzerland), G. Dietler (Fribourg, Switzerland), M. Binggeli, R. Christoph (Neuchâtel, Switzerland) and O. Marti (Konstanz, Germany)

Advances in coating and thin film characterization (Poster session)

Microstructural investigation of the κ-$Al_2O_3 \rightarrow \alpha$-$Al_2O_3$ transformation in multilayer coatings of chemically vapour deposited κ-Al_2O_3..... 311
N. Lindulf, M. Halvarsson, H. Nordén (Göteborg, Sweden) and S. Vuorinen (Fagersta, Sweden)

Advanced image processing in scanning probe microscopy 318
F. K. Urban III, P. Romine and Md. S. Islam (Miami, FL, USA)

Modelling of surface roughness in variable-angle spectroscopic ellipsometry, using numerical processing of atomic force microscopy images 326
F. K. Urban III (Miami, FL, USA), P. Ruzakowski Athey (Pittsburgh, PA, USA) and Md. S. Islam (Miami, FL, USA)

Photoacoustic studies of laser damage in oxide thin films 333
M. Reichling, J. Siegel, E. Matthias (Berlin, Germany), H. Lauth and E. Hacker (Jena, Germany)

Investigations on n-CdO/p-CdTe thin film heterojunctions..... 339
C. Sravani, K. T. R. Reddy, O. Md. Hussain and P. J. Reddy (Tirupati, India)

Microstructure and mechanical properties of sputtered platinum films 344
H. Tokura, B. Window, D. Neely and M. Swain (Lindfield, NSW, Australia)

Residual stress in stabilized zirconia thin films prepared by r.f. magnetron sputtering..... 349
P. Scardi, P. Polonioli and S. Ferrari (Mesiano, Italy)

Residual stress distribution in electroplated Zn–Ni alloy layer detemined by X-ray diffraction 356
T. Sasaki and Y. Hirose (Kanazawa, Japan)

Pin-pull adhesion measurements of copper films on ion-bombarded alumina..... 362
R. A. Erck (Argonne, IL, USA)

TOPICAL SYMPOSIUM ON ADVANCED METALLIZATION

Advanced metallization materials and processes

Al planarization processes for multilayer metallization of quarter micrometer devices 367
Z. Xu, H. Kieu, I. J. Raaijmakers and A. Tepman (Santa Clara, CA, USA)

The effects of collimation on intrinsic stress in sputter-deposited metallic thin films 372
T. Janacek, D. Liu, S. K. Dew, M. J. Brett (Edmonton, Alta., Canada) and T. J. Smy (Ottawa, Ont., Canada)

Formation of low pressure chemically vapour deposited W thin film on silicon dioxide for gate electrode application 377
J. H. Sone, S.-O. Kim, K.-J. Kim, H. S. Kim and H. J. Kim (Seoul, South Korea)

Cu deposition using a permanent magnet electron cyclotron resonance microwave plasma source 382
L. A. Berry, S. M. Gorbatktin and R. L. Rhoades (Oak Ridge, TN, USA)

Bombardment and gas rarefraction effects on the properties of sputtered Ti thin films 386
W. Tsai (Palo Alto, CA, USA), M. L. Brett, S. K. Dew, D. Liu (Edmonton, Alta., Canada), T. Smy (Ottawa, Ont., Canada) and R. N. Tait (Edmonton, Alta., Canada)

Selective electroless copper plating on silicon seeded by copper ion implantation 391
S. Bhansali, D. K. Sood and R. B. Zmood (Melbourne, Australia)

TiN-capped $TiSi_2$ formation in $W/TiSi_2$ process for a quarter-micron complementary metal–oxide–semiconductor 395
Y. Matsubara, M. Sekine, N. Kodama, K. Noguchi and K. Okumura (Sagamihara, Japan)

Gold and zinc thin films deposited by the ionized cluster beam technique 402
S. W. Feng, J. J. Nainaparampil, M. F. Tabet and F. K. Urban III (Miami, FL, USA)

Au/(Ti–W) and Au/Cr metallization of chemically vapor-deposited diamond substrates for multichip module applications 407
I. Meyyappan, A. P. Malshe, H. A. Naseem and W. D. Brown (Fayetteville, AR, USA)

Electrical properties of the p^+-gate electrode of an a-Si/poly-Si double layer 413
S.-O. Kim, K.-J. Kim, H. S. Kim, S. B. Kang, J. H. Sone, J. S. Byun and H. J. Kim (Seoul, South Korea)

Advanced dielectrics and planarization; materials and processes

Numerical simulations of thin film thermal flow 419
H. Liao and T. S. Cale (Tempe, AZ, USA)

Properties of silicon nitride films prepared by magnetron sputtering 425
Y. Hirohata, N. Shimamoto, T. Hino, T. Yamashima and K. Yabe (Sapporo, Japan)

UV-radiation-induced degradation of fluorinated polyimide films 430
L.-H. Chang and N. C. Saha (Mesa, AZ, USA)

The effects of substrate and annealing ambient on the electrical properties of Ta_2O_5 thin films prepared by plasma enhanced chemical vapor deposition 435
S.-O. Kim and H. J. Kim (Seoul, South Korea)

Diffusion barriers

Comparison of chemical vapor deposition of TiN using tetrakis-diethylamino-titanium and tetrakis-dimethylamino-titanium 440
S. C. Sun and M. H. Tsai (Hsinchu, Taiwan)

Single-phase polycrystalline $Ti_{1-x}W_xN$ alloys ($0 \leq x \leq 0.7$) grown by UHV reactive magnetron sputtering: microstructure and physical properties 445
J. H. Moser, F. Tian, O. Haller, D. B. Bergstrom, I. Petrov, J. E. Greene (Urbana, IL, USA) and C. Wiemer (Lausanne, Switzerland)

Silicides

Effect of dimension sealing on the nucleation of C54 $TiSi_2$ 451
Z. Ma, L. H. Allen (Urbana, IL, USA) and D. D. J. Allman (Colorado Springs, CO, USA)

Kinetics of Ni/a-Ge bilayer reactions 456
J. K. Patterson, B. J. Park, K. Ritley, H. Z. Xiao, J. H. Allen and A. Rockett (Urbana, IL, USA)

High resistivity Co and Ti silicide formation on silicon-on-insulator substrates 462
S. L. Hsia (Durham, NC, USA), G. E. McGuire, T. Y. Tan, P. L. Smith and W. T. Lynch (Triangle Park, NC, USA)

Thickness dependence of the properties and thermal stability of PtSi films 467
S. R. Das, K. Sheergar, D.-X. Xu and A. Naem (Ottawa, Ont., Canada)

Chemical vapor deposition of $TiSi_2$ using SiH_4 and $TiCl_4$ 473
M. A. Mendicino, R. P. Southwell and E. G. Seebauer (Urbana, IL, USA)

Thermal stability of silicide on polycrystalline Si 479
Q. Z. Hong (Dallas, TX, USA), S. Q. Hong (Ithaca, NY, USA), F. M. D'Heurle and J. M. E. Harper (Yorktown Heights, NY, USA)

Electrical and structural properties of buried $CoSi_2$ layers in Si(100) grown by molecular beam allotaxy 485
M. Dolle, U. Gassig, H. L. Bay, A. Schüppen and S. Mantl (Jülich, Germany)

Compound semiconductor metallization

Morphology of Al–Ni–Ge ohmic contacts to n-GaAs as a function of contact composition 490
X. W. Lin (Berkeley, CA, USA), W. V. Lampert (Dayton, OH, USA), W. Swider (Berkeley, CA, USA), T. W. Haas (Dayton, OH, USA), P. H. Holloway (Gainesville, FL, USA), J. Washburn and Z. Liliental-Weber (Berkeley, CA, USA)

Non-alloyed, refractory metal contact optimization with shallow implantations of Zn and Mg 496
M. L. Lovejoy, J. C. Zolper, M. E. Sherwin, A. G. Baca, R. J. Shul, D. J. Rieger and J. F. Klem (Albuquerque, NM, USA)

Development of a gate metal etch process for gallium arsenide wafers 501
R. Bammi, T. S. Cale and G. Grivna (Tempe, AZ, USA)

Reliability/manufacturability

Realistic electromigration lifetime projection of VLSI interconnects 508
H. Kawasaki, C. Lee and T.-K. Yu (Austin, TX, USA)

Effects of electro- and stress migration forces on the $1/f\alpha$ noise of patterned thin metal films 513
J. G. Cottle and N. Klonaris (Tampa, FL, USA)

Topical symposium on advanced metallization (Poster session)

Properties of boron coatings used as plasma facing material of fusion device 518
T. Hino, K. Iwamoto, Y. Hirohata, T. Yamashina (Sapporo, Japan), A. Sagara, N. Noda, N. Inoue, Y. Kubota, N. Natsir, O. Motojima (Nagoya, Japan), T. Matsuda, T. Sogabe, K. Kuroda (Kagawa-Ken, Japan) and M. Yabe (Sapporo, Japan)

Transport through multicomponent dual frequency plasma sheaths 522
F. R. Myers (Chandler, AZ, USA), M. W. Peters, M. Ramaswami (Mesa, AZ, USA) and T. S. Cale (Tempe, AZ, USA)

A.c. properties of ZnO thin films prepared by r.f. magnetron sputtering 529
F. S. Mahmood and R. D. Gould (Keele, UK)

Author Index 535

Subject Index 537